

SPE RESPONSE FOR CERTIFICATE OF CORRECTION

Paper No.:20060927

DATE : September 27, 2006

TO SPE OF : ART UNIT 2813

SUBJECT : Request for Certificate of Correction on Patent No.: 7,022,555

A response is requested with respect to the accompanying request for a certificate of correction.

Please complete this form and return with file, within 7 days to:

Certificates of Correction Branch - PK 3-910

Palm location **7590** - Tel. No. 305-8201

With respect to the change(s) requested, correcting Office and/or Applicant's errors, should the patent read as shown in the certificate of correction? No new matter should be introduced, nor should the scope or meaning of the claims be changed.

Thank You For Your Assistance

Certificates of Correction Branch

The request for issuing the above-identified correction(s) is hereby:

Note your decision on the appropriate box.

☒ **Approved**

All changes apply.

☐ **Approved in Part**

Specify below which changes **do not** apply.

☐ **Denied**

State the reasons for denial below..

Comments:



SPE: Carl W. Whitehead, Jr.

Art Unit 2813

**UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION**

Page 1 of 2

PATENT NO. : 7,022,555
APPLICATION NO. : 10/774,515
ISSUE DATE : April 4, 2006
INVENTORS : John T. Moore et al.

It is certified that errors appear in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

In the U.S. Patents portion of the References Cited section, add the following two patents:

4,673,957	6/1987	Ovshinsky et al.
5,335,219	8/1994	Ovshinsky et al.

In the Other Publications portion of the References Cited section, add the following applications:

U.S. Appl. No. 09/779,983, filed Feb. 2001, Moore.
U.S. Appl. No. 09/943,190, filed Aug. 2001, Campbell, et al.
U.S. Appl. No. 09/943,199, filed Aug. 2001, Campbell, et al.
U.S. Appl. No. 09/943,187, filed Aug. 2001, Campbell, et al.
U.S. Appl. No. 10/077,867, filed Feb. 2002, Campbell, et al.
U.S. Appl. No. 10/232,757, filed Aug. 2002, Li, et al.

Also in Other Publications, on page 7, delete the following:

U.S. Appl. No. 5,238,862, filed Aug. 1993, Blalock et al.
U.S. Appl. No. 5,360,981, filed Nov. 1994, Owen, et al.
U.S. Appl. No. 5,761,115, filed Jun. 1998, Kozicki, et al.

MAILING ADDRESS OF SENDER (Please do not use customer number below):

Thomas J. D'Amico
DICKSTEIN SHAPIRO LLP
1825 Eye Street, NW
Washington, DC 20006-5403

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U.S. Appl. No. 5,896,312, filed Apr. 1999, Kozicki et al.

U.S. Appl. No. 5,914,893, filed Jun. 1999, Kozicki et al.

U.S. Appl. No. 6,084,796, filed Jul. 2000, Kozicki et al.

In the Specification, the following error is corrected:

Column 2, line 16, "metal is ion" should read --metal ion--.

In Other Publications, the following typographical errors are corrected:

"Titus, S.S.K.; Chatterjee, R.; Asokan, S., Electrical switching and short-range order in As-Te glasses, Phys. Rev. B 48 (1992) 14650-14652."

Should read

--Titus, S.S.K.; Chatterjee, R.; Asokan, S., Electrical switching and short-range order in As-Te glasses, Phys. Rev. B 48 (1993) 14650-14652.--;

"Hirose, et al., "Polarity-dependent memory switching and behavior of Ag dendrite in Ag-photodoped amorphous As_2S_3 films". Journal of Applied Physics, vol. 47, No. 6, Jun. 1976, pp. 278-2772."

Should read

--Hirose, et al., "Polarity-dependent memory switching and behavior of Ag dendrite in Ag-photodoped amorphous As_2S_3 films". Journal of Applied Physics, vol. 47, No. 6, Jun. 1976, pp. 2767-2772.--.

In Other Publications, Applicants made the following typographical errors to be corrected:

"Tranchant, S.; Peytavin, S.; Ribes, M.; Flank, A.M.; Dexpert, H.; Lagarde, J.P., Silver chalcogenide glasses Ag-Ge-Se: Ionic conduction and exafs structural investigation, Transport-structure relations in fast ion and mixed conductors Proceedings of the 6th Riso International symposium. Sep. 9-13, 1985."

Should read

--Tranchant, S.; Peytavin, S.; Ribes, M.; Flank, A.M.; Dexpert, H.; Lagarde, J.P., Silver chalcogenide glasses Ag-Ge-Se: Ionic conduction and EXAFS structural investigation, Transport-structure relations in fast ion and mixed conductors, Proc. of the 6th RISO Int'l Symp. Sep. 9-13, 1985.--;

"Kotkata, M.F.; Afif, M.A.; Labib, H.H.; Hegab, N.A.; Abdel-Aziz, M.M., Memory switching in amorphous GeSeTe chalcogenide semiconductor films, Thin Solid Films 240 (1994) 143-146."

Should read

--Kotkata, M.F.; Afifi, M.A.; Labib, H.H.; Hegab, N.A.; Abdel-Aziz, M.M., Memory switching in amorphous GeSeTe chalcogenide semiconductor films, Thin Solid Films 240 (1994) 143-146.--.

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AUG 29 2006



Docket No.: M4065.0697/P697-A
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Letters Patent of:
John T. Moore et al.

Patent No.: 7,022,555

Issued: April 4, 2006

For: METHODS OF FORMING A
SEMICONDUCTOR MEMORY DEVICE

REQUEST FOR CERTIFICATE OF CORRECTION
PURSUANT TO 37 C.F.R. §§1.322 & 1.323

Attention: Certificate of Correction Branch
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

Upon reviewing the above-identified patent, Patentees noted typographical and other errors which should be corrected.

In the U.S. Patents portion of the References Cited section, the PTO omitted the following two patents from the IDS dated July 15, 2004 (attached as Exhibit A, Page 1), which should be added:

4,673,957	6/1987	Ovshinsky et al.	08/25/2006 TBESHAN1 00000089 7022555
			01 FC:1811 100.00 OP
5,335,219	8/1994	Ovshinsky et al.	